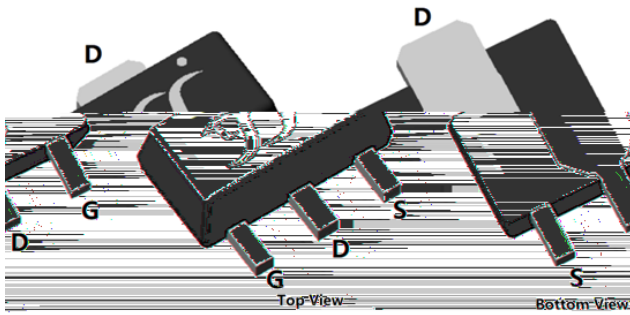




N-Channel Enhancement Mode Field Effect Transistor



Product Summary

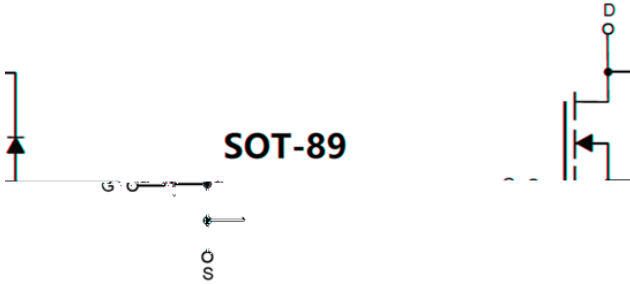
V_{DS}	60V
I_D	5A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	31m
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	38m

General Description

Trench Power LV MOSFET technology
 Excellent package for heat dissipation
 High density cell design for low $R_{DS(ON)}$
 Epoxy Meets UL 94 V-0 Flammability Rating
 Halogen Free

Applications

Power switching application
 Uninterruptible power supply
 DC-DC convertor



SOT-89

(otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25$	I_D	5	A
	$T_A=100$		3	
Pulsed Drain Current ^A		I_{DM}	40	A
Total Power Dissipation ^B	$T_A=25$	P_D	1.78	W
	$T_A=100$		0.71	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +150	

Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^C	Steady-State	R_{θ}	56	70	/W

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJH05N06A	F2	6005A	1000	8000	32000	jjq



YJH05N06A

Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _B 7: 5 F	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	F
		V _{DS} =60V, V _{GS} =0V, T _J =150	-	-	100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _B 7: 5 F	1	1.5	2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5A	-	23	31	r
		V _{GS} =4.5V, I _D =3A	-	27	38	
Diode Forward Voltage	V _{SD}	I _S =5A, V _{GS} =0V	-	-	1.2	V
Gate resistance	R _G	f=1MHz	-	1.7	-	
Maximum Body-Diode Continuous Current	I _S		-	-	5	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f=1MHz	-	1150	-	pF
Output Capacitance	C _{oss}		-	65	-	
Reverse Transfer Capacitance	C _{rss}		-	55	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =30V, I _D =5A	-	22	-	nC
Gate-Source Charge	Q _{gs}		-	3.2	-	
Gate-Drain Charge	Q _{gd}		-	4.3	-	
Reverse Recovery Charge	Q _{rr}	I _F =5A, di/dt=100A/us	-	18	-	nC
Reverse Recovery Time	t _{rr}		-	26	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =30V, I _D =5A R _{GEN} =2.2	-	8	-	ns
Turn-on Rise Time	t _r		-	20	-	
Turn-off Delay Time	t _{D(off)}		-	21	-	
Turn-off fall Time	t _f		-	2	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. P_d is based on max. junction temperature, using junction-case thermal resistance.

C. The value of R_θ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in the still air environment with T_A=25 . The maximum allowed junction temperature of 150 . The value in any given application depends on the user's specific board design.



Typical Electrical and Thermal Characteristics Diagrams



Figure 1. Output Characteristics

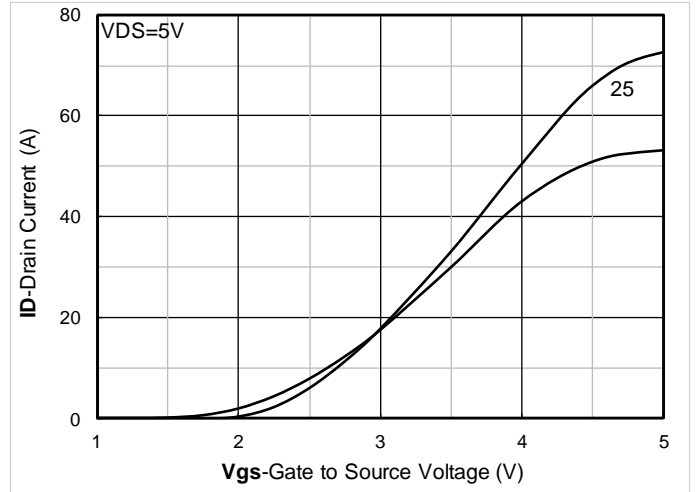


Figure 2. Transfer Characteristics

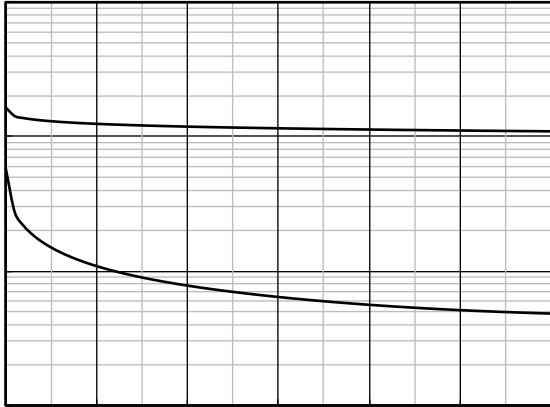


Figure 3. Capacitance Characteristics

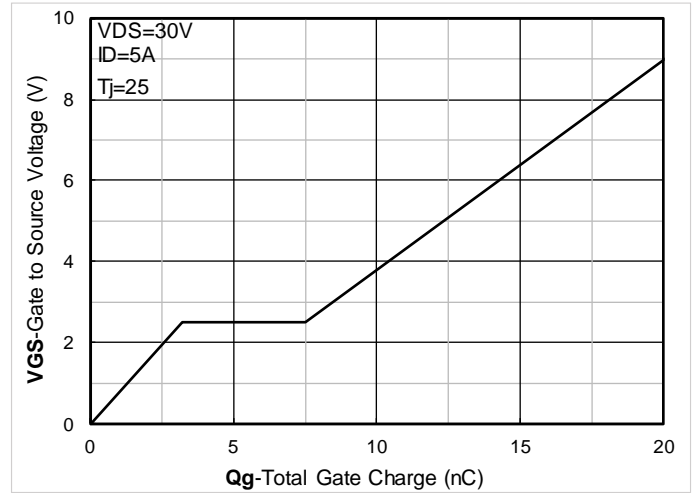


Figure 4. Gate Charge

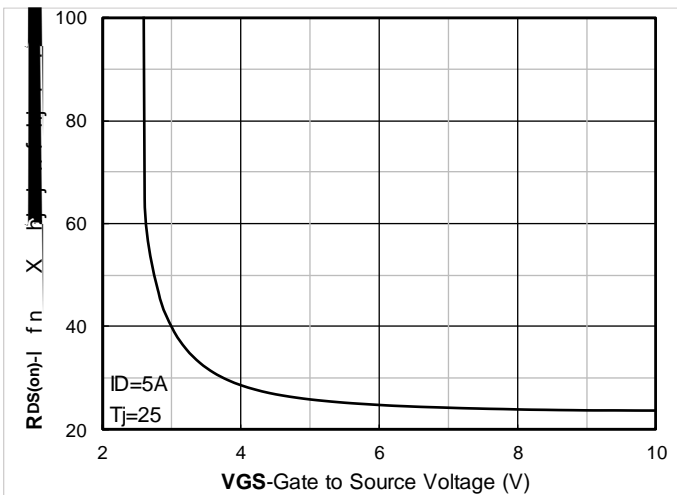


Figure 5. On-Resistance vs Gate to Source Voltage

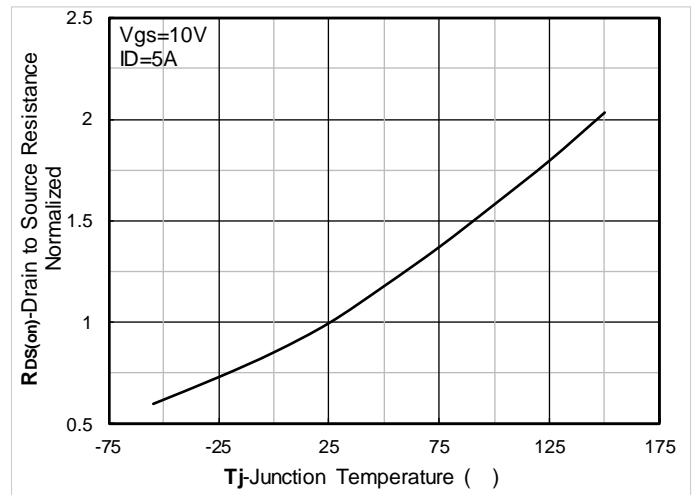


Figure 6. Normalized On-Resistance

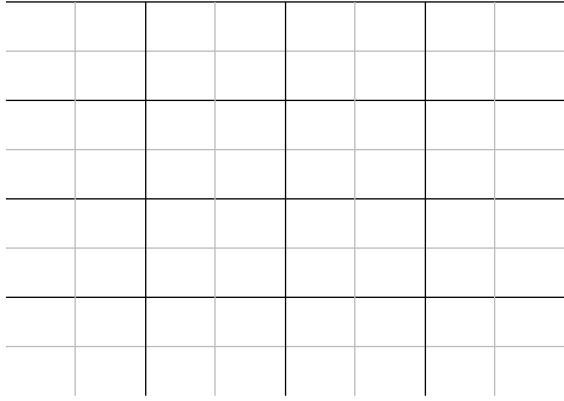


Figure 7. $R_{DS(on)}$ VS Drain Current

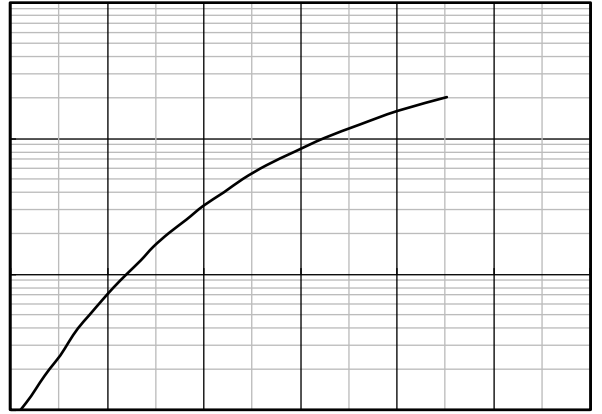


Figure 8. Forward characteristics of reverse diode

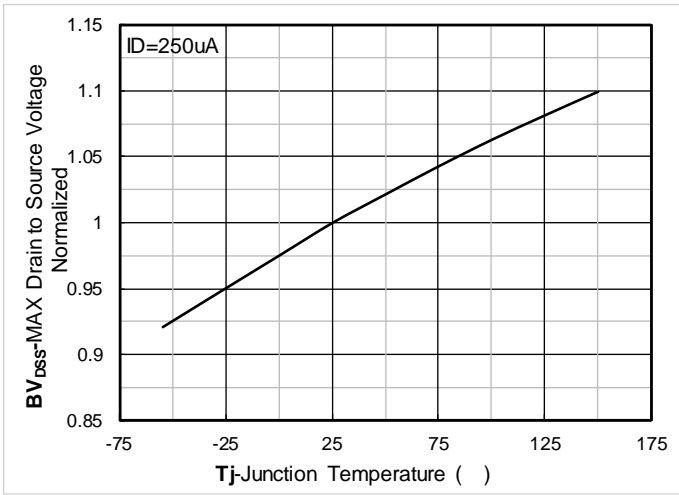


Figure 9. Normalized breakdown voltage

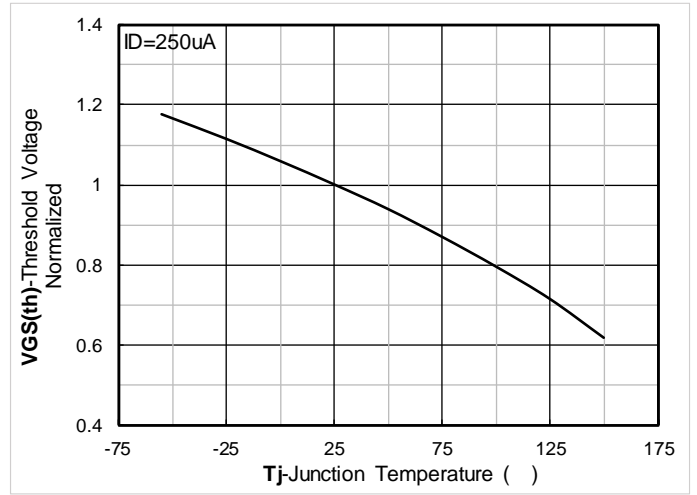


Figure 10. Normalized Threshold voltage

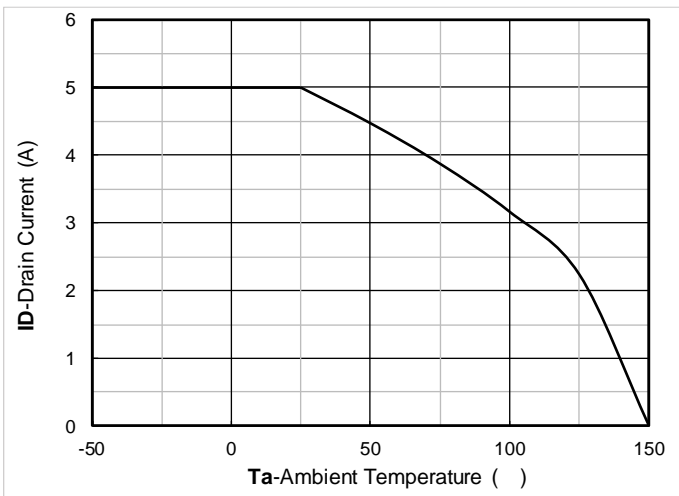


Figure 11. Current dissipation

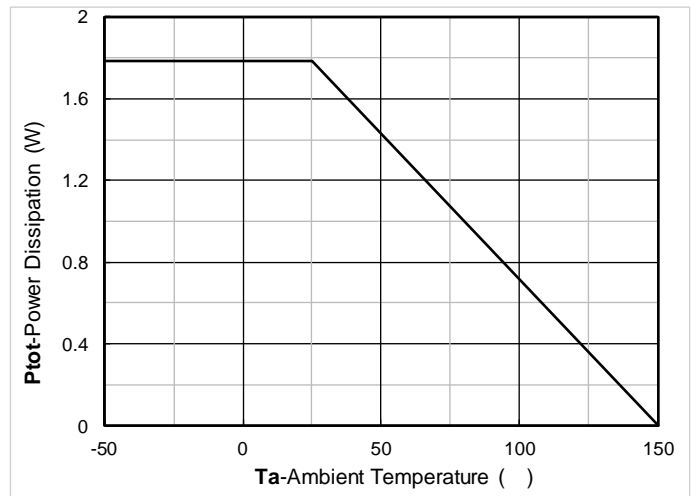


Figure 12. Power dissipation



YJH05N06A

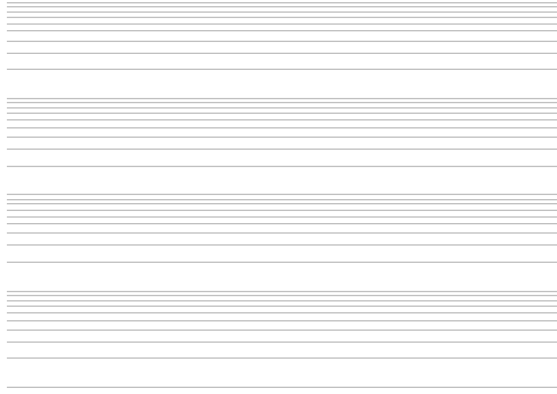


Figure 13. Maximum Transient Thermal Impedance

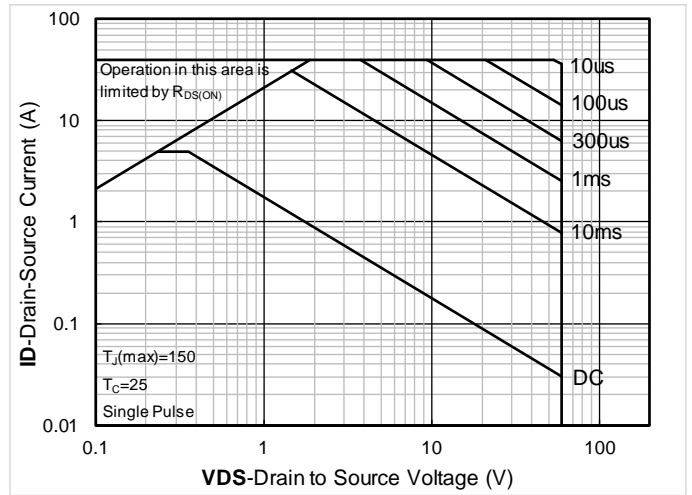
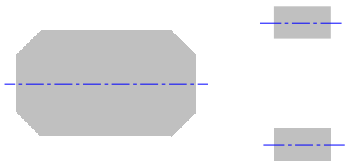
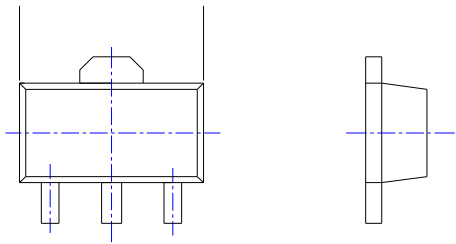


Figure 14. Safe Operation Area



SOT-89 Package information



NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

UNIT mm



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